

1. Scope

The present specifications shall apply to Sanken silicon diode, FMN-G14S.

2. Outline

Type	Silicon Rectifier Diode	
Structure	Resin Molded	Flammability : UL94V-0 (Equivalent)
Applications	High Frequency Rectification	

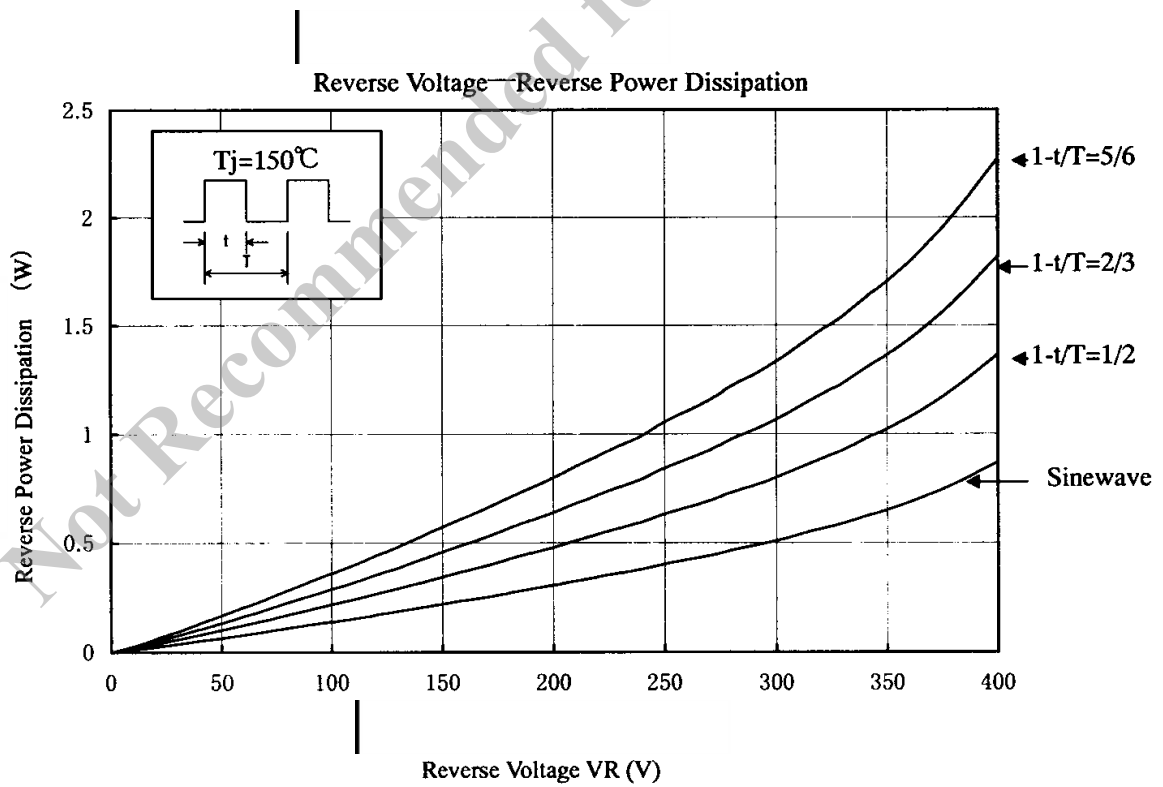
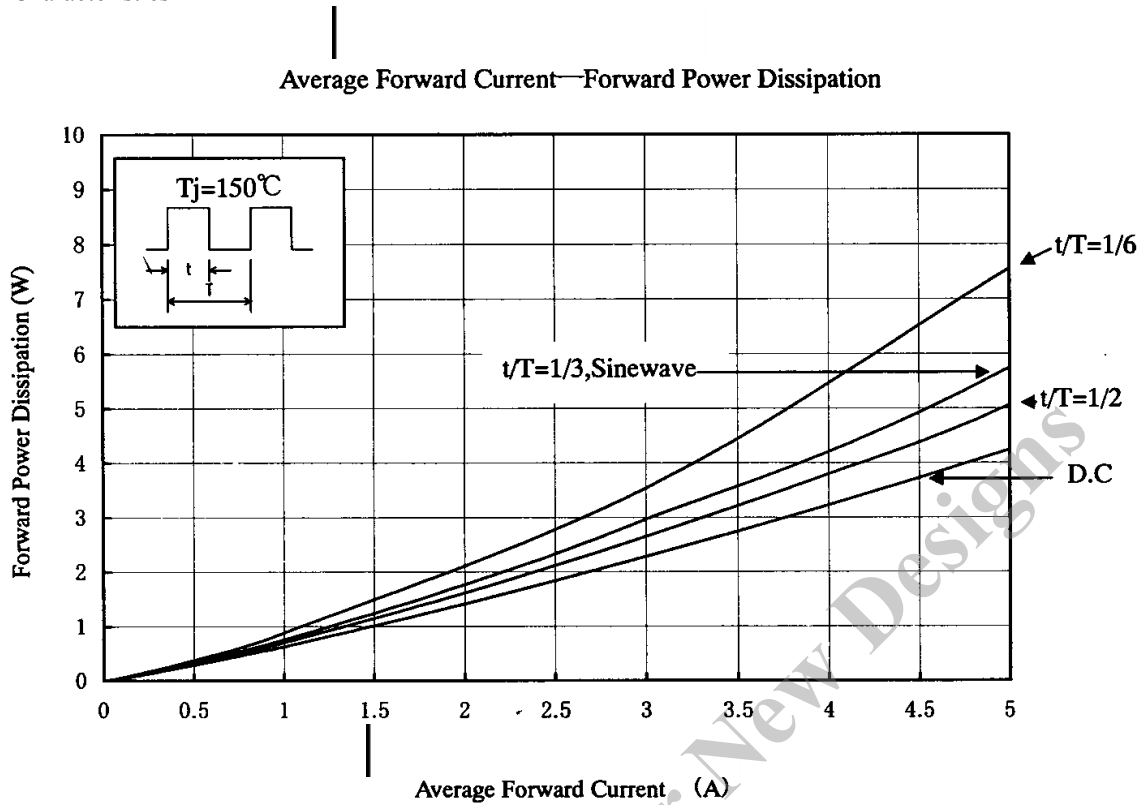
3. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	400	
2	Peak Reverse Voltage	V_{RM}	V	400	
3	Average Forward Current	$I_{F(AV)}$	A	5.0	$T_c=121^\circ\text{C}$, Sinewave
4	Peak Surge Forward Current	I_{FSM}	A	70	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	24.5	$1\text{msec} \leq t \leq 10\text{msec}$
6	Junction Temperature	T_j	$^\circ\text{C}$	-40~+150	
7	Storage Temperature	T_{stg}	$^\circ\text{C}$	-40~+150	
8	Dielectric Strength		kV	A.C. 1.0	Junction and case(1 minute)

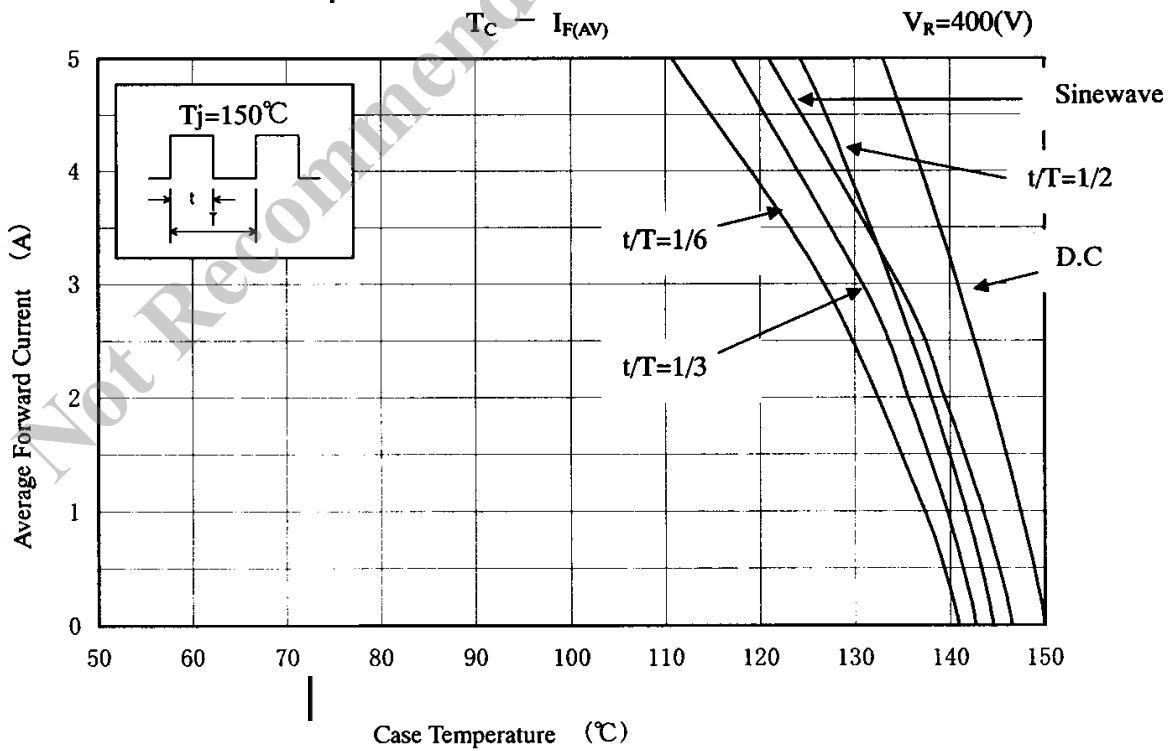
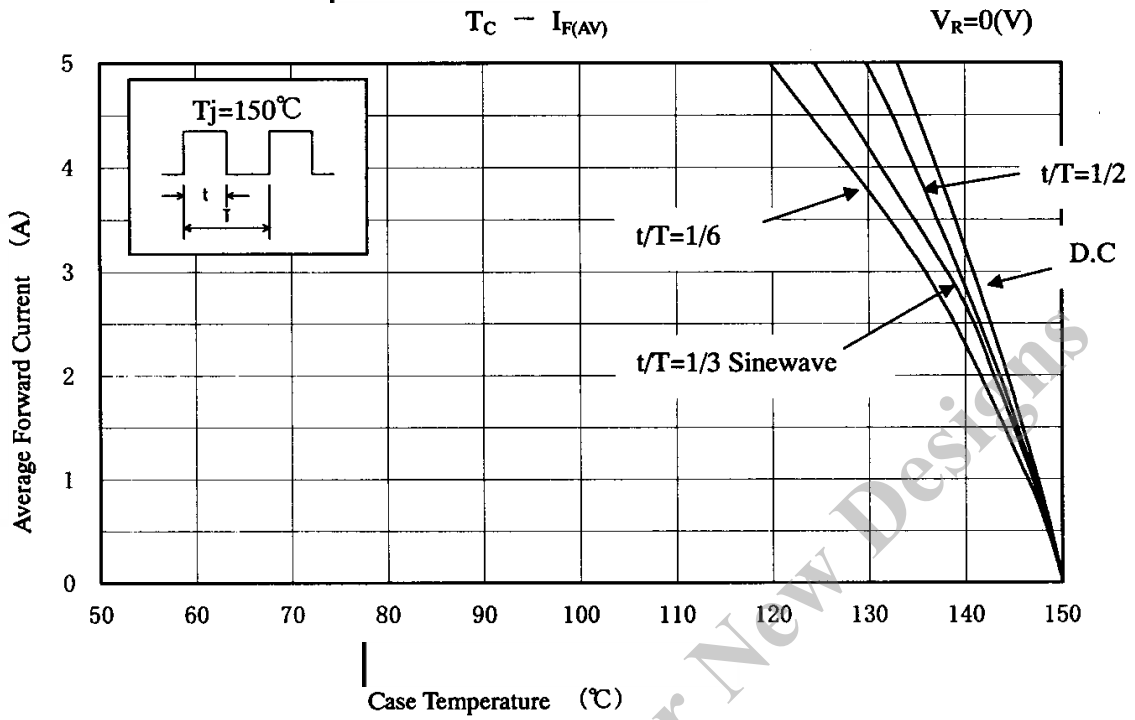
4. Electrical characteristics ($T_a=25^\circ\text{C}$, unless otherwise specified)

No	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.0 max.	$I_F=5.0\text{A}$
2	Reverse Leakage Current	I_R	μA	50 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	10 max.	$V_R=V_{RM}$, $T_j=150^\circ\text{C}$
4	Reverse Recovery Time	trr1	ns	100 max.	$I_F=I_R=500\text{mA}$, $T_j=25^\circ\text{C}$ 90% Recovery point
		trr2	ns	50 max.	$I_F=500\text{mA}$, $I_R=1\text{A}$, $T_j=25^\circ\text{C}$ 75% Recovery point
5	Thermal Resistance	$R_{th(j-c)}$	$^\circ\text{C}/\text{W}$	4.0 max.	Between Junction and case

5. Characteristics

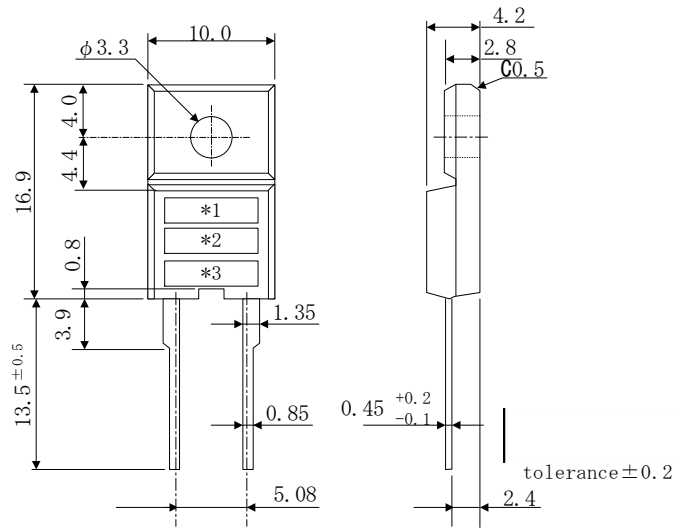


6. 減定格
Derating



7. Package information

7-1 Package type, physical dimensions and material



Dimensions in mm

7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMN-G14S	FMNG14	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 4812 (Aug. 12, 2004)